



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Ying Zhou, et al.

Serial No.: 10/696,204

Filed: October 29, 2003

For: Depositing an Oxide

§ Group Art Unit: 2812

§

§

§

§

§

§

§

Examiner:

Atty. Dkt. No.: ITL.1024US (P16711)

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Dear Sir:

Applicant submits the references listed on the attached form PTO 1449 together with any required copies of such references.

This statement is being filed before the receipt of a first Office action on the merits.

Please apply any charges or credits to Deposit Account 20-1504 (ITL.1024US).

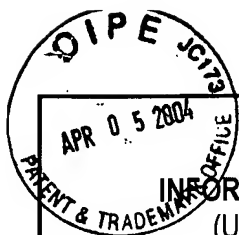
Respectfully submitted,

Date: April 2, 2004

Rhonda L. Sheldon  
Registration No. 50,457  
TROP, PRUNER & HU, P.C.  
8554 Katy Freeway, Suite 100  
Houston, Texas 77024  
(713) 468-8880 [Phone]  
(713) 468-8883 [Fax]

Date of Deposit: **April 2, 2004**  
I hereby certify under 37 CFR 1.8(a) that this correspondence is being deposited with the United States Postal Service as **first class mail** with sufficient postage on the date indicated above and is addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Rebecca R. Ginn

**INFORMATION DISCLOSURE CITATION**

(Use several sheets if necessary)

ATTY DOCKET NO.

ITL.1027US (P16711)

SERIAL NO.

10/696,204

APPLICANT(S):

YING ZHOU, ET AL.

FILING DATE:

October 29, 2003

GROUP ART UNIT:

2812

**U.S. PATENT DOCUMENTS**

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	A.						
	B.						
	C.						
	D.						
	E.						
	F.						
	G.						
	H.						
	I.						

**FOREIGN PATENT DOCUMENTS**

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	J.							
	K.							
	L.							
	M.							
	N.							
	O.							

**OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent Pages, Etc.)

	P.	Robert M. Wallace, "Challenges for the Characterization and Integration of High-k Gate Dielectrics," pp. 1-50, Nov. 2002, <a href="http://www.mtsc.unt.edu/lemd/Presentations/AVS%202002%20Invited%20Talk.pdf">http://www.mtsc.unt.edu/lemd/Presentations/AVS%202002%20Invited%20Talk.pdf</a>
	Q.	Gerry Lucovsky, "The Physics and Chemistry of High-k Dielectrics and their Interfaces," pp. 1-49, available on June 2003, at <a href="http://www.semtech.org/public/news/conferences/Reliability4/Documents/03_Gate_Stack_Transistor_Lucovsky.pdf">http://www.semtech.org/public/news/conferences/Reliability4/Documents/03_Gate_Stack_Transistor_Lucovsky.pdf</a>
	R.	
	S.	
	T.	

EXAMINER

DATE CONSIDERED

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.